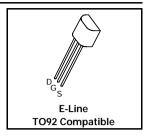
# N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

**ZVN2106A** 

#### ISSUE 2 - MARCH 94

#### **FEATURES**

- \* 60 Volt V<sub>DS</sub>
- \*  $R_{DS(on)} = 2\Omega$



#### ABSOLUTE MAXIMUM RATINGS.

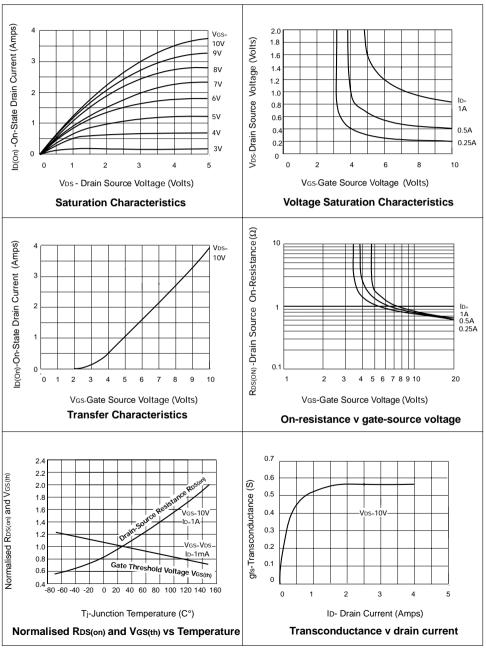
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current at T <sub>amb</sub> =25°C	I <sub>D</sub>	450	mA
Pulsed Drain Current	I <sub>DM</sub>	8	Α
Gate Source Voltage	$V_{GS}$	± 20	V
Power Dissipation at T <sub>amb</sub> =25°C	P <sub>tot</sub>	700	mW
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

## ELECTRICAL CHARACTERISTICS (at T<sub>amb</sub> = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60		V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	0.8	2.4	V	ID=1mA, V <sub>DS</sub> = V <sub>GS</sub>
Gate-Body Leakage	I <sub>GSS</sub>		20	nA	$V_{GS}$ =± 20V, $V_{DS}$ =0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		500 100	nΑ μΑ	V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V <sub>DS</sub> =48 V, V <sub>GS</sub> =0V, T=125°C(2)
On-State Drain Current(1)	I <sub>D(on)</sub>	2		Α	V <sub>DS</sub> =18V, V <sub>GS</sub> =10V
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>		2	Ω	$V_{GS}=10V,I_{D}=1A$
Forward Transconductance (1)(2)	g <sub>fs</sub>	300		mS	$V_{DS}=18V,I_{D}=1A$
Input Capacitance (2)	C <sub>iss</sub>		75	pF	
Common Source Output Capacitance (2)	C <sub>oss</sub>		45	pF	V <sub>DS</sub> =18 V, V <sub>GS</sub> =0V, f=1MHz
Reverse Transfer Capacitance (2)	C <sub>rss</sub>		20	pF	

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#### TYPICAL CHARACTERISTICS



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## TYPICAL CHARACTERISTICS

